

## KSC2518

### High Speed, High Voltage Switching

- Low Collector Saturation Voltage
- Specified of Reverse Biased SOA With Inductive Load



### 1.Base 2.Collector 3.Emitter

# **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	4	Α
I <sub>CP</sub>	*Collector Current (Pulse)	8	Α
I <sub>B</sub>	Base Current (DC)	1	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	40	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

<sup>\*</sup> PW≤350μs, Duty Cycle≤10%

## **Electrical Characteristics** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 2A, I <sub>B1</sub> = 0.4A, L = 1mH	400		V
V <sub>CEX</sub> (sus)1	Collector-Emitter Sustaining Voltage	$I_C = 2A$ , $I_{B1} = -I_{B2} = 0.4A$ $T_a = 125$ °C, L = 180 $\mu$ H, Clamped	450		V
V <sub>CEX</sub> (sus)2	Collector-Emitter Sustaining Voltage	$I_C = 4A$ , $I_{B1} = 0.8A$ , $-I_{B2} = 0.4A$ $T_a = 125$ °C, $L = 180\mu H$ , Clamped	400		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 400V, I_{E} = 0$		10	μΑ
I <sub>CER</sub>	Collector Cut-off Current	$V_{CE} = 400V, R_{BE} = 51\Omega @ T_{C} = 125^{\circ}C$		1	mA
I <sub>CEX1</sub>	Collector Cut-off Current	$V_{CE} = 400V, V_{BE}(off) = -1.5V$ $V_{CE} = 400V, V_{BE}(off) = -1.5V$ @ $T_{C} = 125^{\circ}C$		10 1	μA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		10	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	* DC Current Gain	$V_{CE} = 5V, I_{C} = 0.3A$ $V_{CE} = 5V, I_{C} = 1.5A$	20 10	80	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$		1	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A, I <sub>B</sub> = 0.3A		1.5	V
t <sub>ON</sub>	Turn ON Time	V <sub>CC</sub> = 150V, I <sub>C</sub> = 2A		1	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 0.4A$		2.5	μs
t <sub>F</sub>	Fall Time	$R_L = 75\Omega$		0.7	μs

<sup>\*</sup> Pulse Test: PW≤350μs, Duty Cycle≤2% Pulsed

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE1</sub>	20 ~ 40	30 ~ 60	40 ~ 80

# **Typical Characteristics**

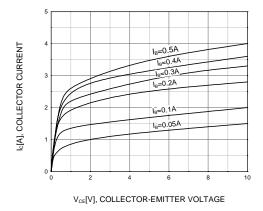


Figure 1. Static Characteristic

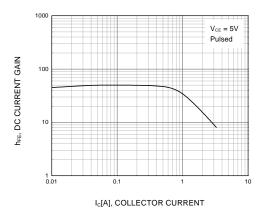


Figure 2. DC current Gain

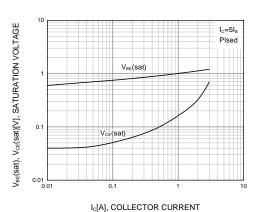


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

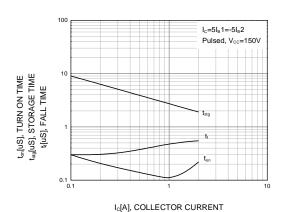


Figure 4. Turn On, Storage and Fall Time vs Collector Current

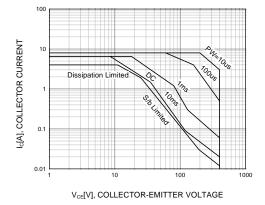
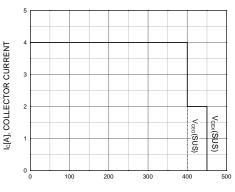


Figure 5. Forward Bias Safe Operating Area



 $V_{CE}(s)$ , COLLECTOR-EMITTER VOLTAGE

Figure 6. Reverse Bias Safe Operating Area

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# **Typical Characteristics** (Continued)

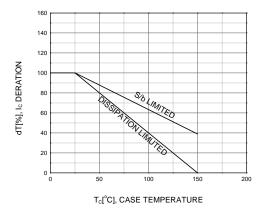


Figure 7. Derating Curve of Safe Operating Areas

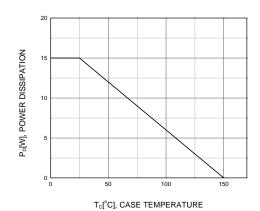
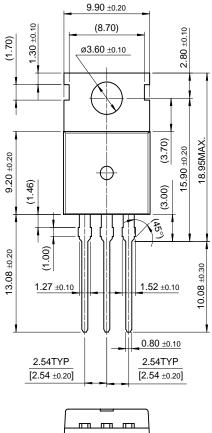
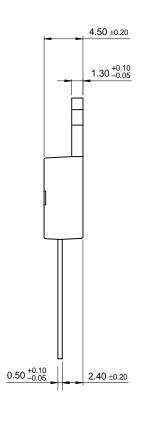


Figure 8. Power Derating

# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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